

isc Silicon NPN Darlington Power Transistor

2SD1410

DESCRIPTION

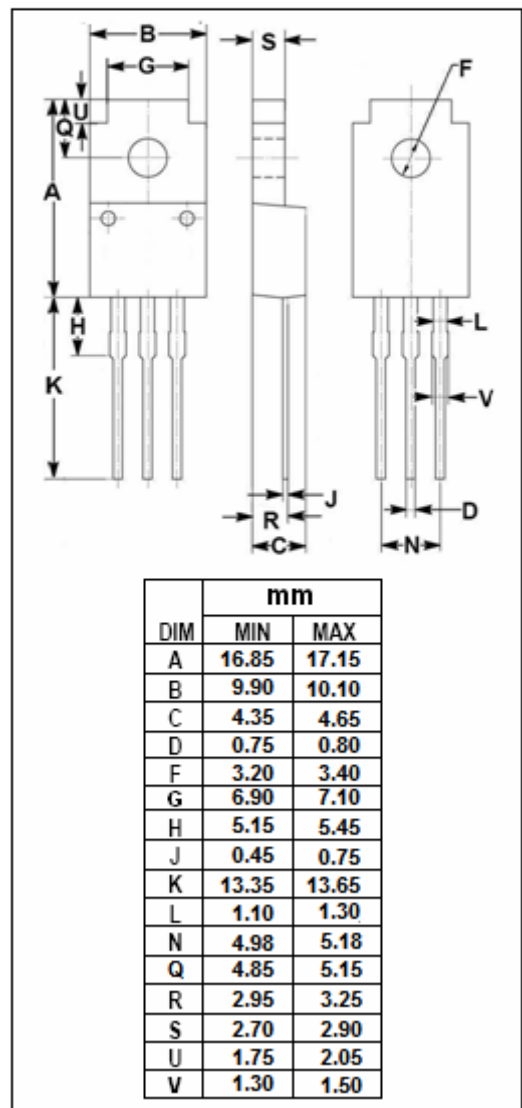
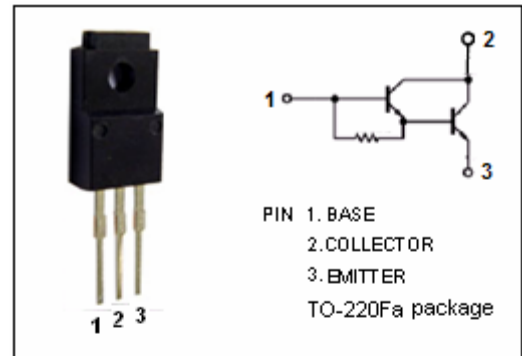
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 250V(\text{Min})$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 2.0V(\text{Max}) @ I_C = 4A$
- High DC Current Gain
: $h_{FE} = 2000(\text{Min}) @ I_C = 2A, V_{CE} = 2V$

APPLICATIONS

- Igniter applications
- High voltage switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	250	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	6	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2.0	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	30	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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